

4V Drive Pch MOSFET

RT1E050RP

● Structure

Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) High power package.
- 3) 4V drive.

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RT1E050RP		○

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DSS}	-30	V
Gate-source voltage	V_{GSS}	±20	V
Drain current	Continuous	I_D	±5 A
	Pulsed	I_{DP} *1	±20 A
Source current (Body Diode)	Continuous	I_S	-1 A
	Pulsed	I_{SP} *1	-20 A
Power dissipation	P_D *2	1.25	W
Channel temperature	T_{ch}	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

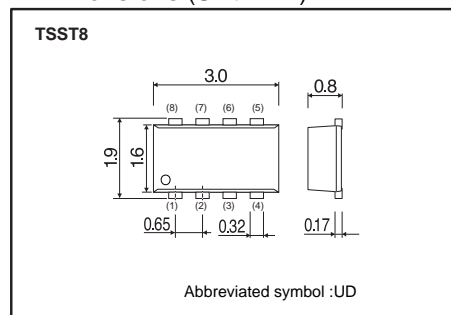
*2 Mounted on a ceramic board.

● Thermal resistance

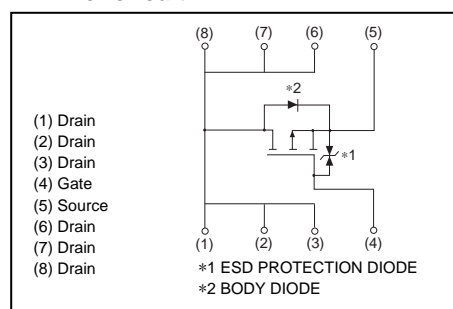
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-a)$ *	100	°C / W

*Mounted on a ceramic board.

● Dimensions (Unit : mm)



● Inner circuit



● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D=-1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	-1	μA	$V_{DS}=-30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS}=-10V, I_D=-1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	26	36	m Ω	$I_D=-5A, V_{GS}=-10V$
		-	36	50		$I_D=-2.5A, V_{GS}=-4.5V$
		-	40	56		$I_D=-2.5A, V_{GS}=-4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	3.1	-	-	S	$I_D=-5A, V_{DS}=-10V$
Input capacitance	C_{iss}	-	1300	-	pF	$V_{DS}=-10V$
Output capacitance	C_{oss}	-	180	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	160	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	10	-	ns	$I_D=-2.5A, V_{DD}=-15V$
Rise time	t_r^*	-	15	-	ns	$V_{GS}=-10V$
Turn-off delay time	$t_{d(off)}^*$	-	90	-	ns	$R_L=6.0\Omega$
Fall time	t_f^*	-	50	-	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	-	13	-	nC	$I_D=-5A, V_{DD}=-15V$
Gate-source charge	Q_{gs}^*	-	3.5	-	nC	$V_{GS}=-5V, R_L=3\Omega$
Gate-drain charge	Q_{gd}^*	-	4.5	-	nC	$R_G=10\Omega$

*Pulsed

● Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	-1.2	V	$I_s=-5A, V_{GS}=0V$

*Pulsed

● Electrical characteristics curves

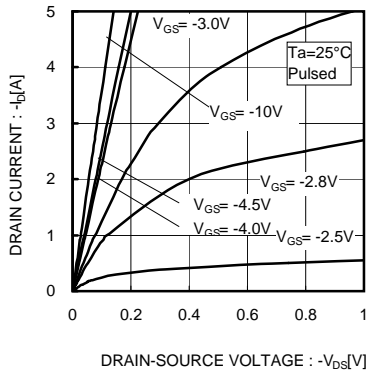


Fig.1 Typical Output Characteristics (I)

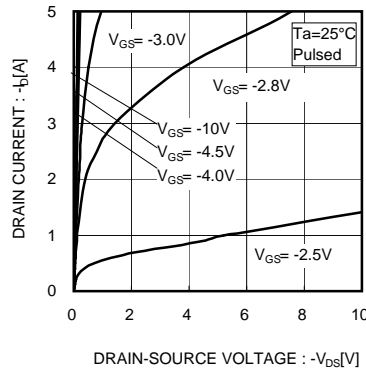


Fig.2 Typical Output Characteristics (II)

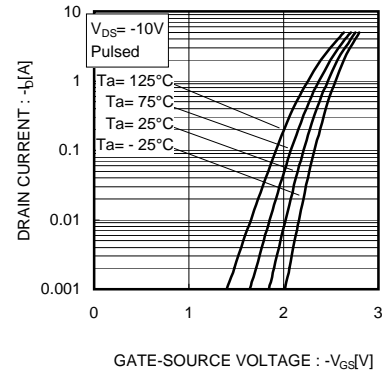


Fig.3 Typical Transfer Characteristics

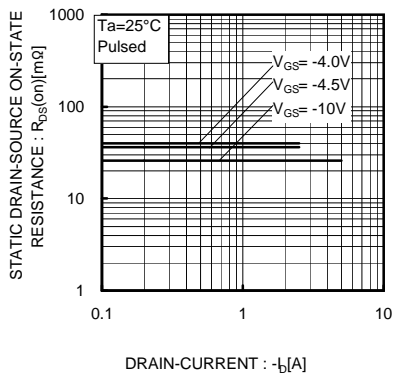


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

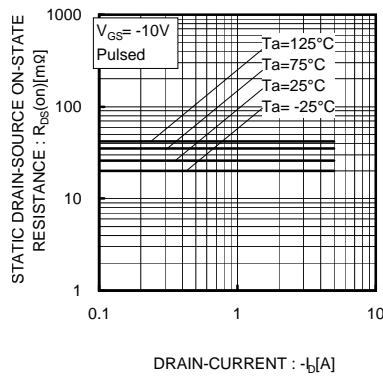


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

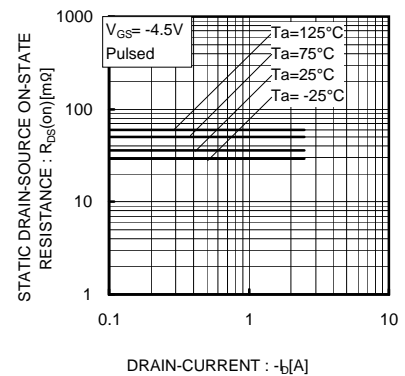


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (III)

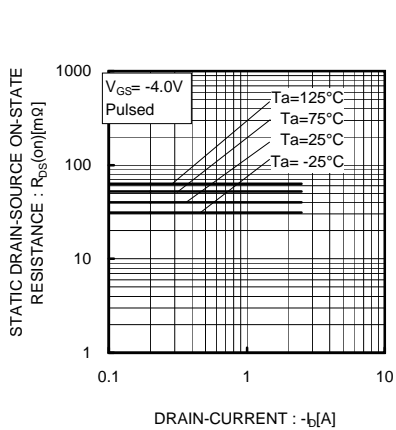


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (IV)

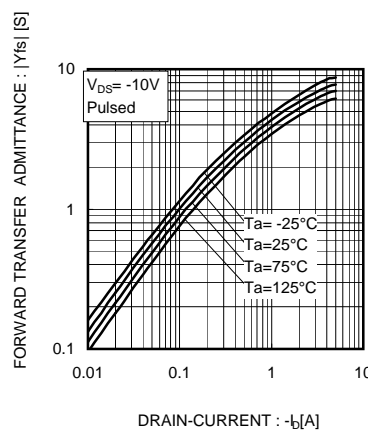


Fig.8 Forward Transfer Admittance vs. Drain Current

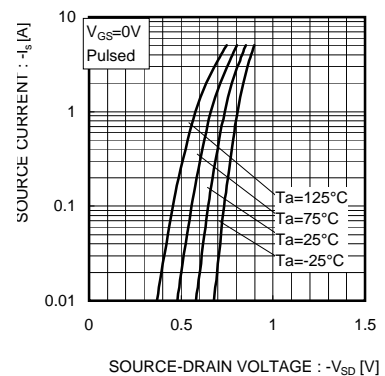


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

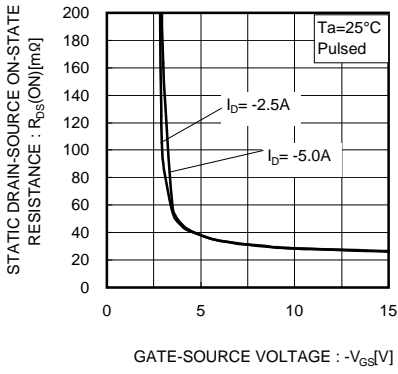


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

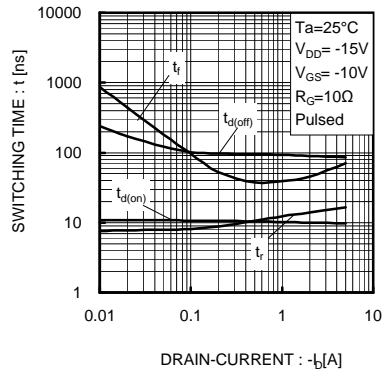


Fig.11 Switching Characteristics

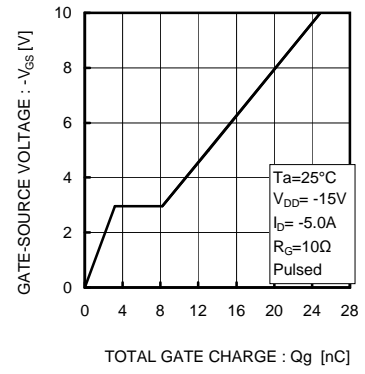


Fig.12 Dynamic Input Characteristics

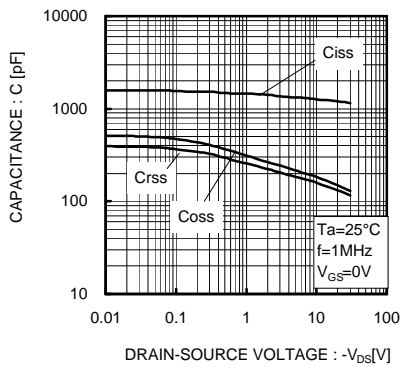


Fig.13 Typical Capacitance vs. Drain-Source Voltage

● Measurement circuits

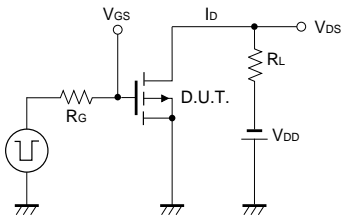


Fig.1-1 Switching Time Measurement Circuit

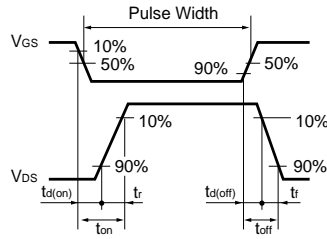


Fig.1-2 Switching Waveforms

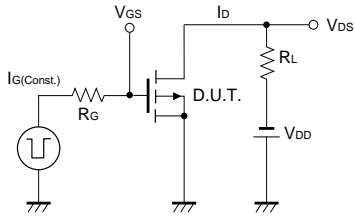


Fig.2-1 Gate Charge Measurement Circuit

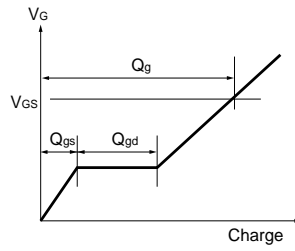


Fig.2-2 Gate Charge Waveform

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